

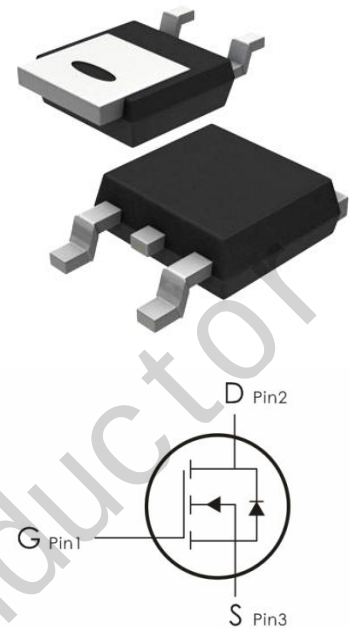
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=30A, R_{DS(on)} < 30m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	30	A
	Continuous Drain Current- $T_C=100^\circ C$	16	
I_{DM}	Drain Current - Pulsed1	100	A
E_{AS}	Single Pulse Avalanche Energy (note1)	24	mJ
I_{AS}	Avalanche Current (note2)	22	A
P_D	Power Dissipation	40	W
	Power Dissipation - Derate above $25^\circ C$	0.32	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	

Electrical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V,I _D =250 μ A	60	---	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25℃ , ID=1mA	---	0.07	---	V/℃
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =650V	---	---	1	μ A
		V _{GS} =0V, V _{DS} =480V,T _J =125℃	---	---	10	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 30V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.2	1.7	2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =10V,I _D =15A	---	25	30	m Ω
		V _{GS} =4.5V,I _D =10A	---	31	40	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	1150	1700	pF
C _{oss}	Output Capacitance		---	60	90	
C _{rss}	Reverse Transfer Capacitance		---	43	65	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time ^{2,3}	V _{DD} =30V, I _D =1A, R _G =6 Ω (Note 3,4)	---	15	40	ns
t _r	Rise Time ^{2,3}		---	4.5	8	ns
t _{d(off)}	Turn-Off Delay Time ^{2,3}		---	27	50	ns

t_f	Fall Time ^{2,3}		---	7.5	13	ns
Q_g	Total Gate Charge ^{2,3}	V _{GS} =30V, V _{DS} =10V, I _D =20A(Note 3,4)	---	16	20	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	2	4	nC
Q_{gd}	Gate-Drain “Miller” Charge ^{2,3}		---	3.5	7	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =1A,	---	---	1	V
I_S	Continuous Source Current	---	---	---	25	A
I_{SM}	Pulsed Source Current	---	---	---	100	A
T_{rr}	Reverse Recovery Time	V _{GS} =0V,I _S =1A , dI/dt=100A/μs(Note 3)	---	17	---	ns
Q_{rr}	Reverse Recovery Charge		---	12	---	nC

Notes:

- 1.Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=22A, R_G=25\ \Omega$, Starting $T_J=25^\circ C$
- 3.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.Essentially independent of operating temperature.

Typical Characteristics: ($T_c=25^\circ C$ unless otherwise noted)

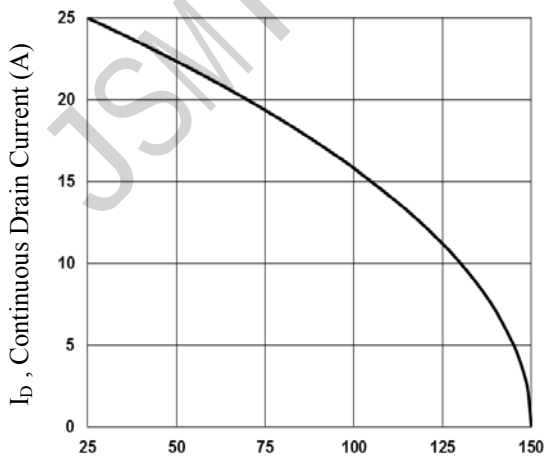


Fig.1 Continuous Drain Current vs. T_c

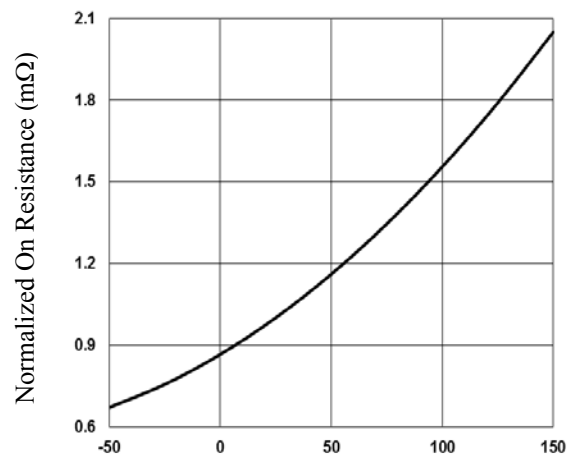
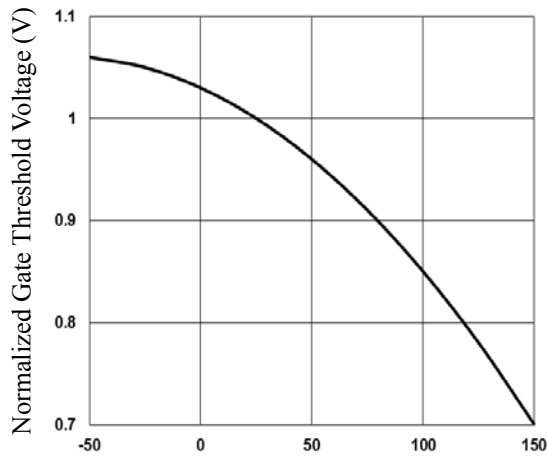
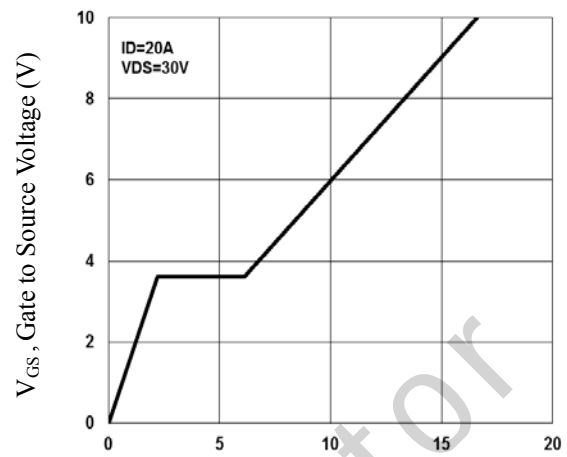
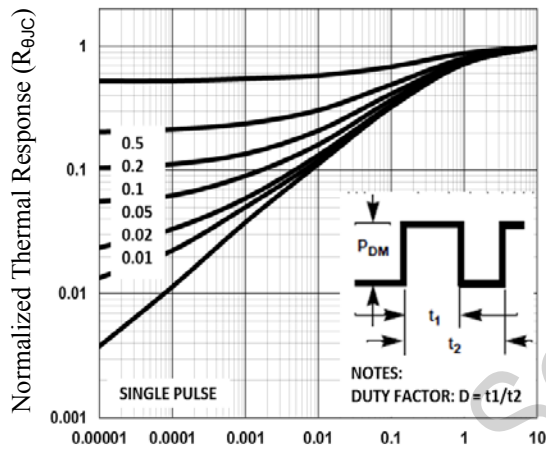
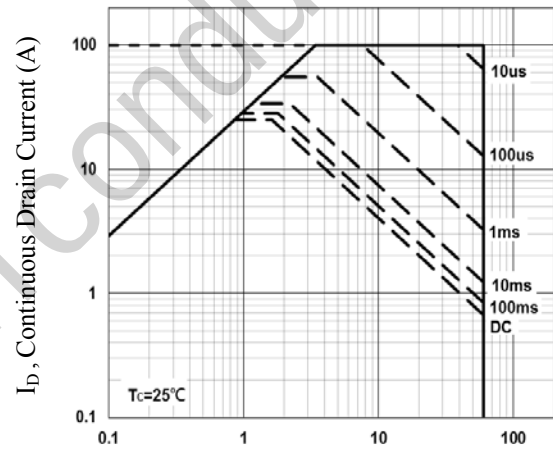
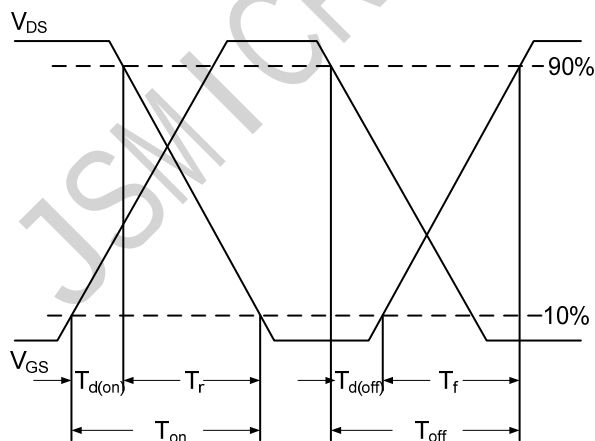
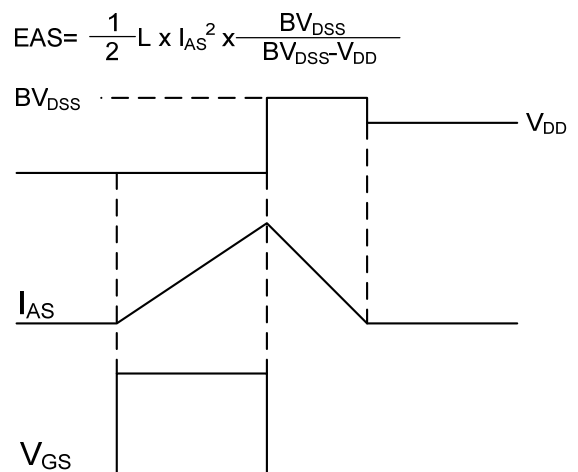


Fig.2 Normalized $R_{DS(on)}$ vs. T_J


Fig.3 Normalized V_{th} vs. T_j

Fig.4 Gate Charge Waveform

Fig.5 Normalized Transient Impedance

Fig.6 Maximum Safe Operation Area

Fig.7 Switching Time Waveform

Fig.8 EAS Waveform

外形尺寸图 / Package Dimensions

